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# **D-Type Flip-Flop with Asynchronous Clear**

## **NL17SZ175**

The NL17SZ175 is a single, positive edge triggered, D-type CMOS Flip-Flop with Asynchronous Clear operating from a 1.65 V to 5.5 V supply.

#### **Features**

- Designed for 1.65 V to 5.5 V V<sub>CC</sub> Operation
- 2.6 ns  $t_{PD}$  at  $V_{CC} = 5 \text{ V (Typ)}$
- Inputs/Outputs Overvoltage Tolerant up to 5.5 V
- I<sub>OFF</sub> Supports Partial Power Down Protection
- Sink 32 mA at 4.5 V
- Available in SC-88, SC-74 and UDFN6 Packages
- Chip Complexity < 100 FETs
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

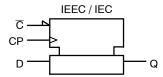
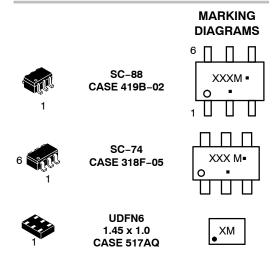


Figure 1. Logic Symbol



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1

UDFN6 1.0 x 1.0 CASE 517BX



X, XXX = Specific Device Code

M = Date Code\*
W = Work Week
■ Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or position may vary depending upon manufacturing location.

### **ORDERING INFORMATION**

See detailed ordering, marking and shipping information in the package dimensions section on page 7 of this data sheet.

### **Connection Diagrams**

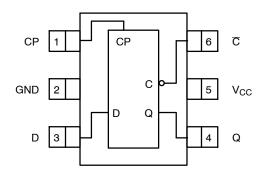


Figure 2. SC-88/SC-74 (Top View)

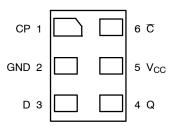


Figure 3. UDFN6(Top Through View)

### **PIN DESCRIPTIONS**

Pin Name	Description
D	Data Input
СР	Clock Pulse Input
C	Clear Input
Q	Flip-Flop Output

### **FUNCTION TABLE**

	Output		
СР	D	C	Q
\	L	Н	L
\	Н	Н	Н
/	Х	Н	Qn
Х	Х	L	L

H = HIGH Logic Level L = LOW Logic Level

Qn = No Change in Data X = Immaterial

### **MAXIMUM RATINGS**

Symbol	Characteristics		Value	Unit
V <sub>CC</sub>	DC Supply Voltage		-0.5 to +6.5	V
V <sub>IN</sub>	DC Input Voltage		-0.5 to +6.5	V
V <sub>OUT</sub>	Tri-S	(High or Low State) tate Mode (Note 1) Mode (V <sub>CC</sub> = 0 V)	-0.5 to V <sub>CC</sub> + 0.5 -0.5 to +6.5 -0.5 to +6.5	V
I <sub>IK</sub>	DC Input Diode Current	V <sub>IN</sub> < GND	-50	mA
I <sub>OK</sub>	DC Output Diode Current	V <sub>OUT</sub> < GND	-50	mA
lout	DC Output Source/Sink Current		±50	mA
I <sub>CC</sub> or I <sub>GND</sub>	DC Supply Current per Supply Pin or Ground Pin		±100	mA
T <sub>STG</sub>	Storage Temperature Range		-65 to +150	°C
T <sub>L</sub>	Lead Temperature, 1 mm from Case for 10 secs		260	°C
TJ	Junction Temperature Under Bias		+150	°C
θ <sub>JA</sub>	Thermal Resistance (Note 2)	SC-88 SC-74 UDFN6	377 320 154	°C/W
P <sub>D</sub>	Power Dissipation in Still Air	SC-88 SC-74 UDFN6	332 390 812	mW
MSL	Moisture Sensitivity		Level 1	-
F <sub>R</sub>	Flammability Rating Oxyg	gen Index: 28 to 34	UL 94 V-0 @ 0.125 in	-
V <sub>ESD</sub>		luman Body Model rged Device Model	2000 1000	V
I <sub>Latchup</sub>	Latchup Performance (Note 4)		±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Applicable to devices with outputs that may be tri-stated.
- Measured with minimum pad spacing on an FR4 board, using 10mm-by-1inch, 2 ounce copper trace no air flow per JESD51-7.
   HBM tested to ANSI/ESDA/JEDEC JS-001-2017. CDM tested to EIA/JESD22-C101-F. JEDEC recommends that ESD qualification to EIA/JESD22-A115-A (Machine Model) be discontinued per JEDEC/JEP172A.
- 4. Tested to EIA/JESD78 Class II.

### RECOMMENDED OPERATING CONDITIONS

Symbol	Cha	Min	Max	Unit	
V <sub>CC</sub>	Positive DC Supply Voltage		1.65	5.5	V
V <sub>IN</sub>	DC Input Voltage		0	5.5	V
V <sub>OUT</sub>	DC Output Voltage	Active-Mode (High or Low State) Tri-State Mode (Note 1) Power-Down Mode (V <sub>CC</sub> = 0 V)	0 0 0	V <sub>CC</sub> 5.5 5.5	
T <sub>A</sub>	Operating Temperature Range		-55	+125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time	$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$ $V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$ $V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$ $V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	0 0 0	20 20 10 5	ns

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

### DC ELECTRICAL CHARACTERISTICS

			V <sub>CC</sub>	T,	λ = 25°C	2	-55°C ≤ T	<sub>A</sub> ≤ 125°C	
Symbol	Parameter	Condition	(V)	Min	Тур	Max	Min	Max	Units
V <sub>IH</sub>	High-Level Input		1.65 to 1.95	0.65 V <sub>CC</sub>	-	_	0.65 V <sub>CC</sub>	-	V
	Voltage		2.3 to 5.5	0.70 V <sub>CC</sub>	-	_	0.70 V <sub>CC</sub>	-	
V <sub>IL</sub>	Low-Level Input		1.65 to 1.95	-	-	0.35 V <sub>CC</sub>	-	0.35 V <sub>CC</sub>	V
	Voltage		2.3 to 5.5	-	-	0.30 V <sub>CC</sub>	-	0.30 V <sub>CC</sub>	
V <sub>OH</sub>	High-Level Output Voltage	$\begin{split} &V_{IN} = V_{IH} \text{ or } V_{IL} \\ &I_{OH} = -100  \mu\text{A} \\ &I_{OH} = -4 \text{ mA} \\ &I_{OH} = -8 \text{ mA} \\ &I_{OH} = -16 \text{ mA} \\ &I_{OH} = -24 \text{ mA} \\ &I_{OH} = -32 \text{ mA} \\ \\ &V_{IN} = V_{IH} \text{ or } V_{IL} \end{split}$	1.65 to 5.5 1.65 2.3 3 3 4.5	V <sub>CC</sub> - 0.1 1.29 1.9 2.4 2.3 3.8	V <sub>CC</sub> 1.52 2.1 2.7 2.5 4	- - - - -	V <sub>CC</sub> - 0.1 1.29 1.9 2.4 2.3 3.8	- - - - -	V V
	Voltage	I <sub>OH</sub> = 100 μA I <sub>OH</sub> = 4 mA I <sub>OH</sub> = 8 mA I <sub>OH</sub> = 16 mA I <sub>OH</sub> = 24 mA I <sub>OH</sub> = 32 mA	1.65 to 5.5 1.65 2.3 3 3 4.5	- - - - -	- 0.08 0.12 0.24 0.26 0.31	0.1 0.24 0.3 0.4 0.55 0.55	- - - - -	0.1 0.24 0.3 0.4 0.55 0.55	
I <sub>IN</sub>	Input Leakage Current	$V_{IN} = 5.5 \text{ V or GND}$	1.65 to 5.5	-	-	±0.1	-	±1.0	μΑ
I <sub>OFF</sub>	Power Off Leakage Current	V <sub>IN</sub> = 5.5 V or V <sub>OUT</sub> = 5.5 V	0	_	ı	1.0	_	10	μА
I <sub>CC</sub>	Quiescent Supply Current	V <sub>IN</sub> = V <sub>CC</sub> or GND	5.5	-	-	1.0	-	10	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

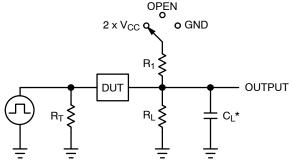
### **AC ELECTRICAL CHARACTERISTICS**

					T <sub>A</sub> = +25°C	;	$T_A = -40$	to +85°C	
Symbol	Parameter	V <sub>CC</sub> (V)	Conditions	Min	Тур	Max	Min	Max	Unit
f <sub>MAX</sub>	Maximum Clock Frequency	1.65	C <sub>L</sub> = 50 pF,	-	-	-	100	-	MHz
	(Figure 4, 5)	1.8	$R_L = 500 \Omega$	_	-	-	100	-	
		2.3 to 2.7		_	-	-	125	-	
		3.0 to 3.6		-	-	-	150	-	
		4.5 to 5.5		-	-	-	175	-	
t <sub>PLH</sub> , t <sub>PHL</sub>	Propagation Delay, CP to Q	1.65	C <sub>L</sub> = 15 pF,	-	9.8	15.0	-	16.5	ns
	(Figure 4, 5)	1.8	$R_L = 1 M\Omega$	-	6.5	10.0	-	11.0	
		2.3 to 2.7		-	3.8	6.5	-	7.0	
		3.0 to 3.6		-	2.8	4.5	-	5.0	
		4.5 to 5.5		-	2.2	3.5	-	3.8	
		3.0 to 3.6	C <sub>L</sub> = 50 pF,	-	3.4	5.5	-	6.2	
		4.5 to 5.5	$R_L = 500 \Omega$	-	2.6	4.0	-	4.7	
t <sub>PHL</sub>	PHL Propagation Delay, C to Q	1.65	C <sub>L</sub> = 15 pF,	-	9.8	13.5	-	15.0	ns
	(Figure 4, 5)	1.8	$R_L = 1 M\Omega$	-	6.5	9.0	-	10.0	
		2.3 to 2.7		-	3.8	6.0	-	6.4	
	3.0 to 3.6		-	2.8	4.3	-	4.6		
		4.5 to 5.5		-	2.2	3.2	-	3.5	
		3.0 to 3.6	$C_L = 50 \text{ pF},$ $R_L = 500 \Omega$	-	3.4	5.3	-	5.8	
		4.5 to 5.5		-	2.7	4.0	-	4.5	
t <sub>S</sub>	Setup Time, CP to D	2.3 to 2.7	C <sub>L</sub> = 50 pF,	-	-	-	2.5	-	ns
	(Figure 4, 5)	3.0 to 3.6	$R_L = 500 \Omega$	-	-	-	2.0	-	1
		4.5 to 5.5		-	-	-	1.5	-	
t <sub>H</sub>	Hold Time, CP to D	2.3 to 2.7	C <sub>L</sub> = 50 pF,	-	-	-	1.5	-	ns
	(Figure 4, 5)	3.0 to 3.6	$R_L = 500 \Omega$	-	-	-	1.5	-	
		4.5 to 5.5		-	-	-	1.5	-	
t <sub>W</sub>	Pulse Width, CP	2.3 to 2.7	C <sub>L</sub> = 50 pF,	-	-	-	3.0	-	ns
	(Figure 4, 5)	3.0 to 3.6	$R_L = 500 \Omega$	-	-	-	2.8	-	
		4.5 to 5.5		-	-	-	2.5	-	
	Pulse Width, C	2.3 to 2.7	Clock HIGH	-	-	-	3.0	-	ns
	(Figure 4, 5)	3.0 to 3.6	or LOW $C_L = 50 \text{ pF},$	-	-	-	2.8	-	
		4.5 to 5.5	$R_L = 500 \Omega$	_	-	-	2.5	-	
t <sub>rec</sub>	Recovery Time,	2.3 to 2.7	C <sub>L</sub> = 50 pF,	-	-	-	1.0	-	ns
	(Figure 4, 5)	3.0 to 3.6	$R_L = 500 \Omega$	_	-	-	1.0	-	1
		4.5 to 5.5	1	_	-	_	1.0	-	

### **CAPACITIVE CHARACTERISTICS**

Symbol	Parameter	Condition	Typical	Units
C <sub>IN</sub>	Input Capacitance	$V_{CC}$ = 5.5 V, $V_{IN}$ = 0 V or $V_{CC}$	2.5	pF
C <sub>OUT</sub>	Output Capacitance	$V_{CC} = 5.5 \text{ V}, V_{IN} = 0 \text{ V or } V_{CC}$	4.0	pF
C <sub>PD</sub>	Power Dissipation Capacitance (Note 5)	10 MHz, $V_{CC}$ = 5.5 V, $V_{IN}$ = 0 V or $V_{CC}$	4.0	pF

CPD is defined as the value of the internal equivalent capacitance which is derived from dynamic operating current consumption (I<sub>CCD</sub>) at no output loading and operating at 50% duty cycle. CPD is related to ICCD dynamic operating current by the expression:  $I_{CCD} = (C_{PD}) (V_{CC}) (f_{IN}) + (I_{CC}static).$ 



t<sub>PLZ</sub> / t<sub>PZL</sub> GND  $t_{PHZ}$  /  $t_{PZH}$ X = Don't Care

Test

t<sub>PLH</sub> / t<sub>PHL</sub>

Switch

**Position** 

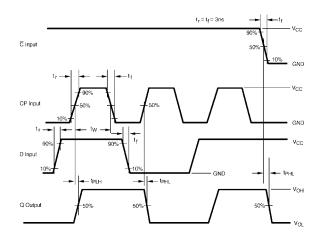
Open

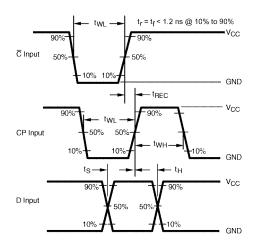
 $2 \times V_{CC}$ 

C<sub>L</sub> includes probe and jig capacitance  $R_T$  is  $Z_{OUT}$  of pulse generator (typically 50  $\Omega$ )

f = 1 MHz

Figure 4. Test Circuit





 $C_L, pF$ 

50

 $R_L, \Omega$ 

500

See AC Characteristics Table

 $R_1,\,\Omega$ 

500

Figure 5. Switching Waveforms

		V <sub>m</sub>		
V <sub>CC</sub> , V	V <sub>mi</sub> , V	t <sub>PLH</sub> , t <sub>PHL</sub>	$t_{PZL}, t_{PLZ}, t_{PZH}, t_{PHZ}$	V <sub>Y</sub> , V
1.65 to 1.95	V <sub>CC</sub> /2	V <sub>CC</sub> / 2	V <sub>CC</sub> / 2	0.15
2.3 to 2.7	V <sub>CC</sub> /2	V <sub>CC</sub> / 2	V <sub>CC</sub> / 2	0.15
3.0 to 3.6	V <sub>CC</sub> /2	V <sub>CC</sub> / 2	V <sub>CC</sub> / 2	0.3
4.5 to 5.5	V <sub>CC</sub> /2	V <sub>CC</sub> / 2	V <sub>CC</sub> / 2	0.3

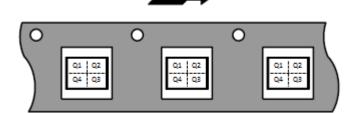
### **DEVICE ORDERING INFORMATION**

Device	Packages	Specific Device Code	Pin 1 Orientation (See below)	Shipping <sup>†</sup>
NL17SZ175DFT2G (In Development)	SC-88	TBD	Q4	3000 / Tape & Reel
NL17SZ175DBVT1G	SC-74	AT	Q4	3000 / Tape & Reel
NL17SZ175MU1TCG (In Development)	UDFN6, 1.45 x 1.0, 0.5P	TBD	Q4	3000 / Tape & Reel
NL17SZ175MU3TCG (In Development)	UDFN6, 1.0 x 1.0, 0.35P	TBD	Q4	3000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

### Pin 1 Orientation in Tape and Reel

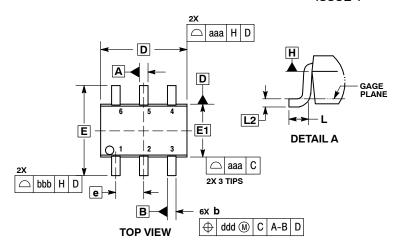
### Direction of Feed

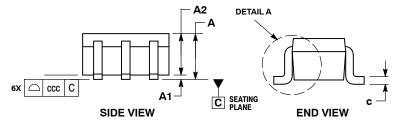


#### PACKAGE DIMENSIONS

### SC-88/SC70-6/SOT-363

CASE 419B-02 **ISSUE Y** 





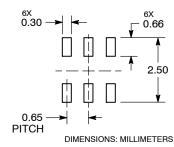
- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: MILLIMETERS.
  3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
  4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
  5. DATUMS A AND B ARE DETERMINED AT DATUM H.
  6. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
  7. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION

- DIMENSION 5 DOES NOT INCLUDE DAMBAR PROTRUSION.
  ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN
  EXCESS OF DIMENSION 5 AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER

	MIL	LIMETE	RS		INCHES	3	
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α			1.10			0.043	
A1	0.00		0.10	0.000		0.004	
A2	0.70	0.90	1.00	0.027	0.035	0.039	
b	0.15	0.20	0.25	0.006	0.008	0.010	
С	0.08	0.15	0.22	0.003	0.006	0.009	
D	1.80	2.00	2.20	0.070	0.078	0.086	
E	2.00	2.10	2.20	0.078	0.082	0.086	
E1	1.15	1.25	1.35	0.045	0.049	0.053	
е		0.65 BS	С	0	.026 BS	С	
L	0.26	0.36	0.46	0.010	0.014	0.018	
L2		0.15 BSC			0.006 BS	SC	
aaa		0.15			0.006		
bbb		0.30			0.012		
ccc		0.10		0.004			
ddd		0.10			0.004		

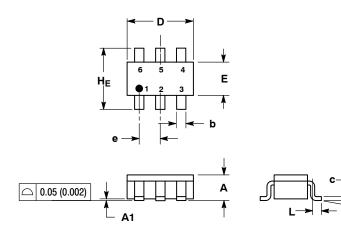
#### **RECOMMENDED SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### **PACKAGE DIMENSIONS**

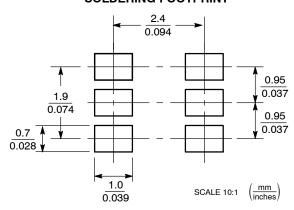
SC-74 CASE 318F-05 **ISSUE N** 



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH
  THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM
  THICKNESS OF BASE MATERIAL.
  4. 318F-01, -02, -03, -04 OBSOLETE. NEW STANDARD 318F-05.

	MILLIMETERS				INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.90	1.00	1.10	0.035	0.039	0.043	
A1	0.01	0.06	0.10	0.001	0.002	0.004	
b	0.25	0.37	0.50	0.010	0.015	0.020	
С	0.10	0.18	0.26	0.004	0.007	0.010	
D	2.90	3.00	3.10	0.114	0.118	0.122	
E	1.30	1.50	1.70	0.051	0.059	0.067	
е	0.85	0.95	1.05	0.034	0.037	0.041	
L	0.20	0.40	0.60	0.008	0.016	0.024	
HE	2.50	2.75	3.00	0.099	0.108	0.118	
θ	0°	_	10°	0°	_	10°	

### **SOLDERING FOOTPRINT\***

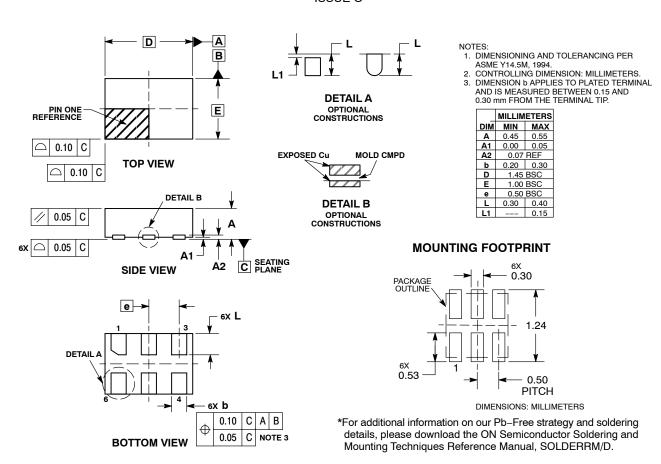


\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLE 1:	STYLE 2:	STYLE 3:	STYLE 4:	STYLE 5:	STYLE 6:
PIN 1. CATHODE	PIN 1. NO CONNECTION	PIN 1. EMITTER 1	PIN 1. COLLECTOR 2	PIN 1. CHANNEL 1	PIN 1. CATHODE
2. ANODE	2. COLLECTOR	2. BASE 1	2. EMITTER 1/EMITTER 2	2. ANODE	2. ANODE
<ol><li>CATHODE</li></ol>	<ol><li>EMITTER</li></ol>	<ol><li>COLLECTOR 2</li></ol>	3. COLLECTOR 1	<ol><li>CHANNEL 2</li></ol>	<ol><li>CATHODE</li></ol>
<ol><li>CATHODE</li></ol>	4. NO CONNECTION	4. EMITTER 2	4. EMITTER 3	<ol><li>CHANNEL 3</li></ol>	<ol><li>CATHODE</li></ol>
5. ANODE	<ol><li>COLLECTOR</li></ol>	5. BASE 2	<ol><li>BASE 1/BASE 2/COLLECTOR 3</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>CATHODE</li></ol>
<ol><li>CATHODE</li></ol>	6. BASE	<ol><li>COLLECTOR 1</li></ol>	6. BASE 3	<ol><li>CHANNEL 4</li></ol>	<ol><li>CATHODE</li></ol>
STYLE 7: PIN 1. SOURCE 1 2. GATE 1 3. DRAIN 2 4. SOURCE 2 5. GATE 2 6. DRAIN 1	STYLE 8: PIN 1. EMITTER 1 2. BASE 2 3. COLLECTOR 2 4. EMITTER 2 5. BASE 1 6. COLLECTOR 1	STYLE 9: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2	STYLE 10: PIN 1. ANODE/CATHODE 2. BASE 3. EMITTER 4. COLLECTOR 5. ANODE 6. CATHODE	STYLE 11: PIN 1. EMITTER 2. BASE 3. ANODE/CATHOD 4. ANODE 5. CATHODE 6. COLLECTOR	E

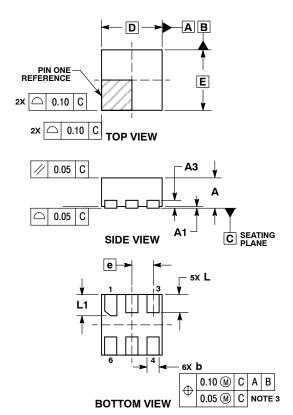
#### **PACKAGE DIMENSIONS**

# **UDFN6, 1.45x1.0, 0.5P**CASE 517AQ ISSUE O



#### PACKAGE DIMENSIONS

UDFN6, 1x1, 0.35P CASE 517BX **ISSUE O** 

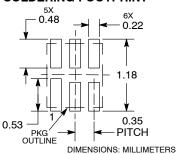


#### NOTES

- DIMENSIONING AND TOLERANCING PER
- ASME Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS.
- DIMENSION & APPLIES TO PLATED
  TERMINAL AND IS MEASURED BETWEEN
- 0.15 AND 0.20 MM FROM TERMINAL TIP. PACKAGE DIMENSIONS EXCLUSIVE OF BURRS AND MOLD FLASH.

	MILLIMETERS	
DIM	MIN	MAX
Α	0.45	0.55
A1	0.00	0.05
A3	0.13 REF	
b	0.12	0.22
D	1.00 BSC	
E	1.00 BSC	
е	0.35 BSC	
L	0.25	0.35
L1	0.30	0.40

#### **RECOMMENDED SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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